## Features

- High Dynamic Range for AM and FM
- Integrated AGC for FM
- High Intercept Point 3rd-order for FM
- FM Amplifier Adjustable to Various Cable Impedances
- High Intercept Point 2nd-order for AM
- Low-noise Output Voltage
- Low-power Consumption

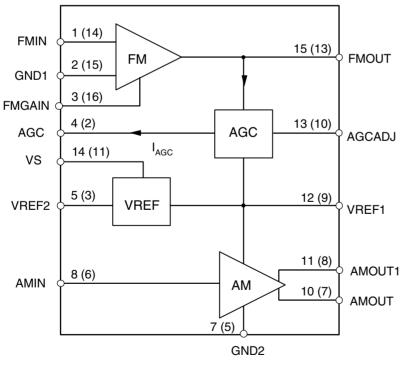
Electrostatic sensitive device. Observe precautions for handling.



# Description

The U4254BM-M is an integrated low-noise AM/FM antenna impedance matching circuit in BiCMOS technology. The device is designed specifically for car applications and is suitable for windshield and roof antennas.

Figure 1. Block Diagram



() Pin numbers in brackets = QFN  $4 \times 4$  package



Low-noise AM/FM Antenna Impedance Matching IC

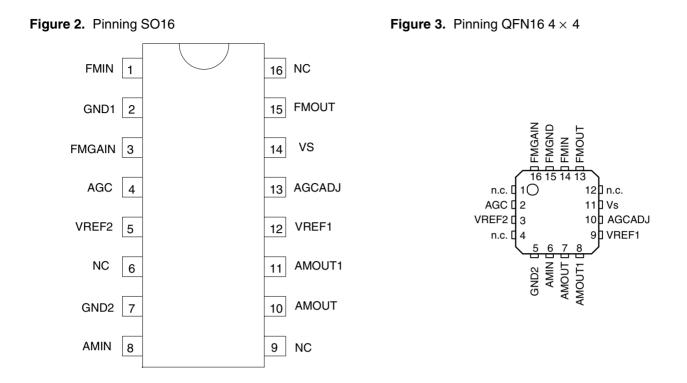
# U4254BM-M

Rev. 4772C-AUDR-08/04





# **Pin Configuration**



# **Pin Description**

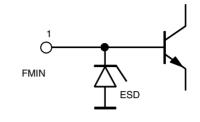
Pin SSO16	Pin QFN16	Symbol	Function	
1	14	FMIN	FM input	
2	15	GND1	Ground for FM part	
3	16	FMGAIN	FM gain adjustment	
4	2	AGC	AGC output	
5	3	VREF2	Reference voltage 2 output	
6	1	NC	Not connected	
7	5	GND2	Ground for AM part	
8	6	AMIN	AM input	
9	4	NC	Not connected	
10	7	AMOUT	AM output	
11	8	AMOUT1	AM output	
12	9	VREF1	Reference voltage 1 output	
13	10	AGCADJ	Adjustment FM wide-band AGC threshold	
14	11	VS	Supply voltage	
15	13	FMOUT	FM output	
16	12	NC	Not connected	

# **Pin Description**

FMIN

FMIN, a bipolar transitor's base is the input of the FM amplifier. A resistor or a coil is connected between FMIN and VREF2. If a coil is used, the noise performance is excellent.

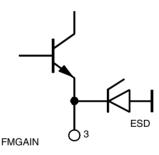
Figure 4. Internal Circuit at Pin FMIN



**GND1** To avoid cross-talk between AM and FM signals, the circuit has two separate ground pins. GND1 is the ground for the FM part.

**FMGAIN** The DC current of the FM amplifier transistor is adjusted by an external resistor which is connected between FMGAIN and GND1. To influence the AC gain of the amplifier, a resistor is connected in series to a capacitor between FMGAIN and GND1. The capacitor has to shorten frequencies of 100 MHz.

Figure 5. Internal Circuit at pin FMGAIN



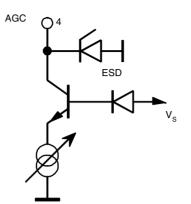
AGC

DC current flows into the AGC pin at high FM antenna input signals. This current has to be amplified via the current gain of an external PNP transistor that feeds a PIN diode. This diode dampens the antenna's input signal and protects the amplifier input against overload. The maximum current which flows in the AGC pin is approximately 1 mA. In low-end applications, the AGC function is not necessary and the external components can therefore be omitted.





Figure 6. Internal Circuit at Pin AGC

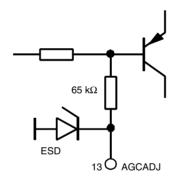


AGCADJ

**FMOUT** 

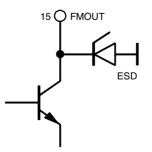
The threshold of the AGC can be adjusted by varying the DC current at pin AGCADJ. If pin AGCADJ is connected directly to GND1, the threshold is set to 96 dB $\mu$ V at the FM amplifier output. If a resistor is connected between AGCADJ and GND1, the threshold is shifted to higher values with increasing resistances. If AGCADJ is open, the threshold is set to 106 dB $\mu$ V.

Figure 7. Internal Circuit at Pin AGCADJ



The FM amplifier output is an open collector of a bipolar RF transistor. It should be connected to  $\rm V_S$  via a coil.

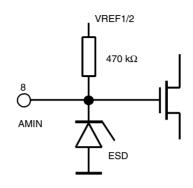
Figure 8. Internal Circuit at Pin FMOUT



AMIN

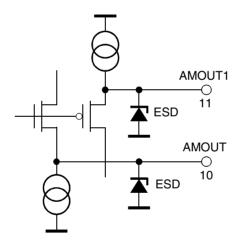
The AM input has an internal bias voltage. The DC voltage at this pin is  $V_{\text{Ref1/2}}$ . The input resistance is about 470 k $\Omega$ . The input capacitance is less than 10 pF.

Figure 9. Internal Circuit at Pin AMIN



AMOUT, AMOUT1 The buffered AM amplifier consists of a complementary pair of CMOS source followers. The transistor gates are connected to AMIN. The pin AMOUT is the NMOS transistor's source, pin AMOUT1 is the PMOS transistor's source. Due to the two different DC levels of these pins, they have to be connected together via an external capacitor of about 100 nF. By means of this technique an excellent dynamic range can be achieved.

Figure 10. Internal Circuit at Pins AMOUT1 and AMOUT



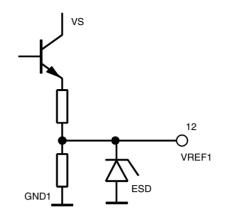
VREF1

VREF1 is the stabilized voltage for the AM amplifier and the AGC block. To achieve excellent noise performance at LW frequencies, it is recommended that this pin be connected to ground via an external capacitor of about 1  $\mu$ F.





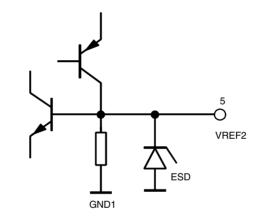
Figure 11. Internal Circuit at Pin VREF1



VREF2

For the DC biasing of the FM amplifier, a second voltage reference circuit is integrated. Since the collector current is temperature independent, the output voltage has a negative temperature coefficient of about -1 mV/K. To stabilize this voltage, an external capacitor to ground of a few nF is recommended.

Figure 12. Internal Circuit at Pin VREF2



GND2

GND2 is the ground for the AM amplifier.

## **Functional Description**

The U4254BM-M is an integrated AM/FM antenna impedance matching circuit. It compensates cable losses between the antenna (for example windshield, roof or bumper antennas) and the car radio which is usually placed far away from the antenna.

The FM amplifier provides excellent noise performance. External components are used to adjust the gain and the input-output matching impedance. Therefore, it is possible to adjust the amplifier to various cable impedances (usually 50, 75 or 150  $\Omega$ ). To protect the amplifier against input overload, an Automatic Gain Control (AGC) is included on the chip. The AGC observes the AC voltage at the FM amplifier output, rectifies this signal, and delivers DC current to dampen the input antenna signal via an external PIN diode. The threshold for the AGC is adjustable. Simple and temperature-compensated biasing is possible due to the integrated voltage reference V<sub>Ref2</sub>.

The AM part consists of a buffer amplifier. The voltage gain of this stage is approximately one. The input resistance is 470 k $\Omega$  the input capacitance less than 10 pF. The output resistance is 125  $\Omega$  An excellent dynamic range is achieved due to the complementary CMOS source follower stage.

## **Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Reference point is ground (pins 2 and 7)

Parameters	Symbol	Value	Unit	
Supply voltage	Vs	8.8	V	
Power dissipation, $P_{tot}$ at $T_{amb} = 85^{\circ}C$	P <sub>tot</sub>	460	mW	
Junction temperature	Tj	150	°C	
Ambient temperature	T <sub>amb</sub>	-40 to +85	°C	
Storage temperature	T <sub>stg</sub>	-50 to +150	°C	
Electrostatic handling (HBM at ESD S.5.1)	±V <sub>ESD</sub>	±1000	V	

## **Thermal Resistance**

Parameters	Symbol	Value	Unit	
Junction ambient	R <sub>thJA</sub>	140	K/W	





# **Electrical Characteristics**

Parameters	Test Conditions	Pin	Symbol	Min.	Тур.	Max.	Unit
Supply voltage		14	Vs	7.2	8	8.8	V
Supply currents		14	ا <sub>s</sub>	3.5	4.8	5.6	mA
Reference voltage 1 output $(I_{12} = 0)$		12	V <sub>Ref1</sub>	5.1	5.4	5.7	V
Reference voltage 2 output $(I_5 = 0)$		5	V <sub>Ref2</sub>	2.3	2.6	2.8	V
Temperature dependence of VREF2		5	$V_{\text{Ref2}}/\Delta T$		-1		mV/K
AM Amplifier		I					
Input resistance		8	R <sub>AMIN</sub>		470		kΩ
Input capacitance		8	C <sub>AMIN</sub>			10	pF
Output resistance		10	R <sub>OUT</sub>		125		Ω
Voltage gain		8, 10	a		0.85		
Output noise voltage (rms value)	S1 switched to 2 B = 6 kHz 150 kHz to 300 kHz 500 kHz to 6.5 kHz	10	V <sub>N1</sub> V <sub>N2</sub>		-2 -6		dBµV dBµV
2nd harmonic	S2 switched to 1 $f_{AMIN} = 500 \text{ kHz}$ Output voltage = 110 dB $\mu$ V	10			-65		dBc
FM Amplifier			·				
Supply current limit	$I_{AGC}, I_{AGCADJ} = 0 A$	15	I <sub>15</sub>		33	35	mA
Input resistance	f = 100 MHz	1	R <sub>FMIN</sub>		50		Ω
Output resistance	f = 100 MHz	15	R <sub>FMOUT</sub>		50		Ω
Power gain	f = 100 MHz	1, 15	G		5		dB
Output noise voltage	f = 100 MHz B = 120 kHz	15	V <sub>N</sub>		0		dBµV
3rd-order output intercept	f = 100 MHz	15			132		dBµV
AGC			·				
AGC input voltage threshold	f = 100 MHz S2 switched to 1; AGC threshold DC current is 10 μA at pin 4	15	V <sub>th1</sub>		96		dBµV
AGC input voltage threshold	$      f = 100 \text{ MHz}, \\ S2 \text{ switched to 2;} \\ AGC threshold DC \\ current is 10 \muA atpin 4$	15	V <sub>th2</sub>		106		dBµV
AGC output current	AGC active		I <sub>AGC</sub>			1.2	mA

 $V_{S} = 8 V$ ,  $T_{amb} = 25^{\circ} C$ , unless otherwise specified (see Figure 13 on page 9).

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Figure 13. Test Circuit

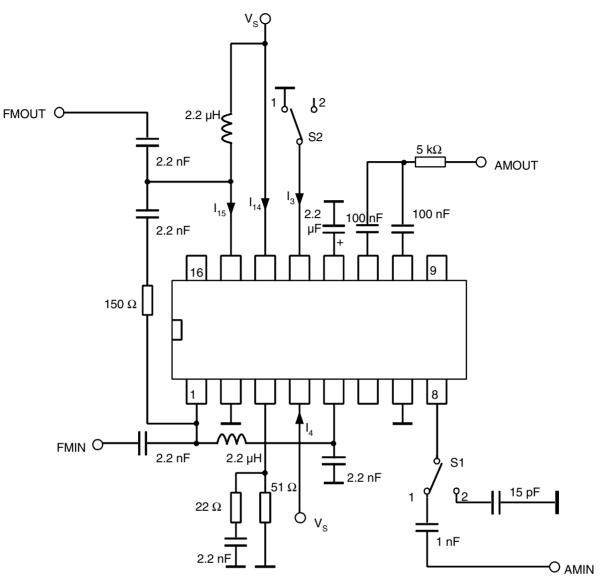
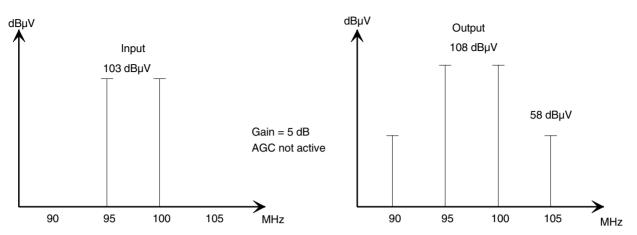
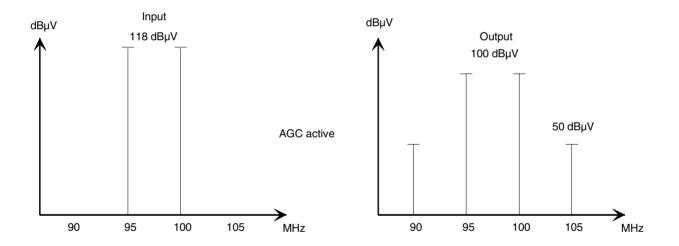




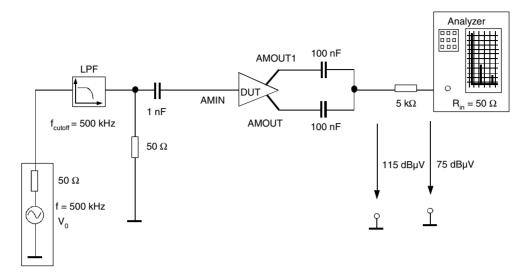


Figure 14. FM Intermodulation Distortion











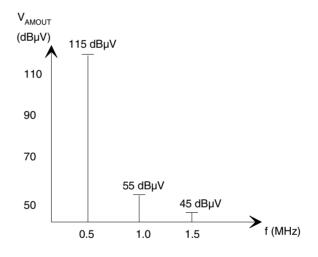
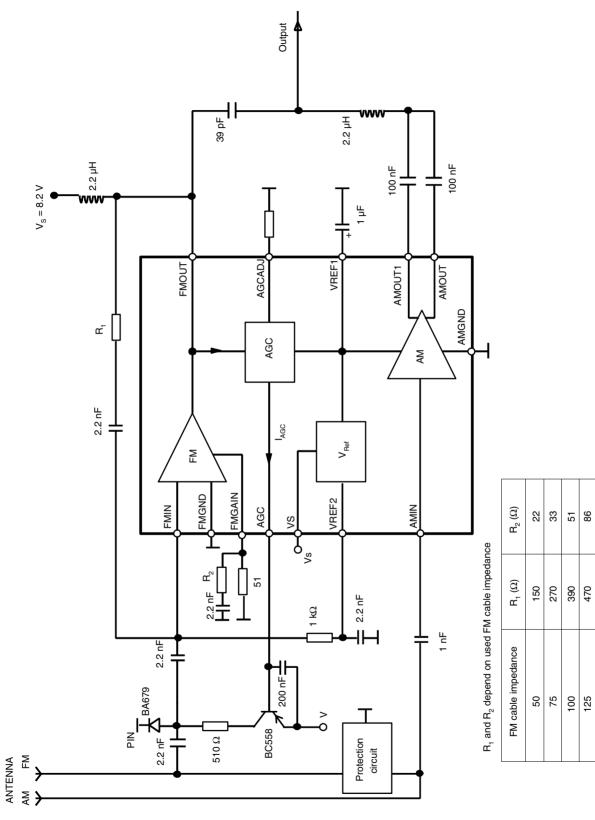






Figure 17. Application Circuit



2 U4254BM-M

160

620

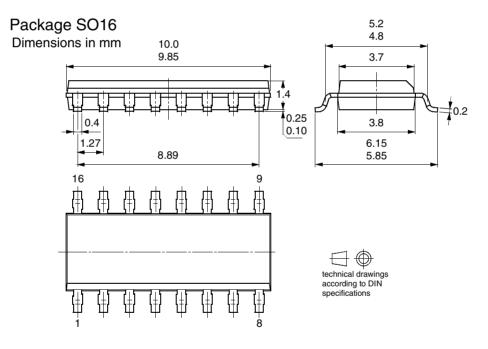
150

12

# **Ordering Information**

Extended Type Number	Package	Remarks
U4254BM-MFP	SO16	-
U4254BM-MPG3	SO16	Taping corresponding, ICE-286-3
U4254BM-MPH	QFN16	-
U4254BM-MPG3H	QFN16	Taping corresponding, ICE-286-3

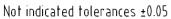
# **Package Information**





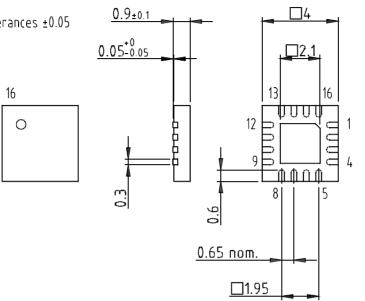


Package: QFN 16 - 4x4 Exposed pad 2.1x2.1 (acc. JEDEC OUTLINE No. MO-220) Dimensions in mm



1

4





technical drawings according to DIN specifications

Drawing-No.: 6.543-5090.01-4 Issue: 2; 24.01.03



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